

## FDP7030BL/FDB7030BL N-Channel Logic Level PowerTrench® MOSFET

### General Description

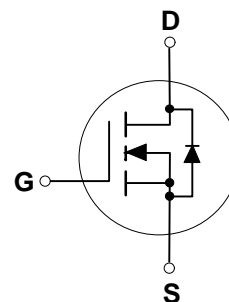
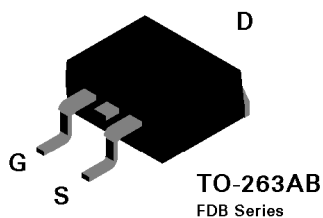
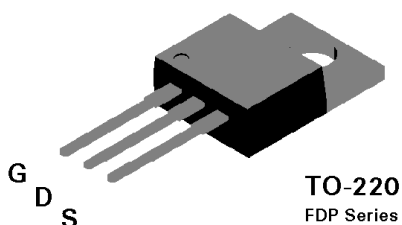
This N-Channel Logic Level MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable  $R_{DS(on)}$  specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

### Features

- 60 A, 30 V.  $R_{DS(on)} = 0.009 \Omega @ V_{GS} = 10 \text{ V}$ ,  
 $R_{DS(on)} = 0.0120 \Omega @ V_{GS} = 4.5 \text{ V}$ .
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- High performance trench technology for extremely low  $R_{DS(on)}$ .
- 175°C maximum junction temperature rating.



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FDP7030BL	FDB7030BL	Units
$V_{DSS}$	Drain-Source Voltage		30	V
$V_{GSS}$	Gate-Source Voltage		$\pm 20$	V
$I_D$	Drain Current - Continuous (Note 1)		60	A
	- Pulsed (Note 1)		180	
$P_D$	Total Power Dissipation @ $T_C = 25^\circ\text{C}$		65	W
	Derate above $25^\circ\text{C}$		0.43	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range		-65 to 175	$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		275	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2.3	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	$^\circ\text{C}/\text{W}$

**Electrical Characteristics** ( $T_c = 25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>DRAIN-SOURCE AVALANCHE RATINGS</b> (Note 1)						
$W_{DSS}$	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 15\text{ V}, I_D = 60\text{ A}$			220	mJ
$I_{AR}$	Maximum Drain-Source Avalanche Current				60	A
<b>OFF CHARACTERISTICS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	30			V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		22		mV/°C
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSSF}$	Gate - Body Leakage, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA
$I_{GSSR}$	Gate - Body Leakage, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA
<b>ON CHARACTERISTICS</b> (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1	1.5	3	V
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Temp. Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-5		mV/°C
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$		0.0073	0.009	$\Omega$
		$T_J = 125^\circ\text{C}$		0.011	0.018	
		$V_{GS} = 4.5\text{ V}, I_D = 25\text{ A}$		0.01	0.012	
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 10\text{ V}$	60			A
$g_{FS}$	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 30\text{ A}$		55		S
<b>DYNAMIC CHARACTERISTICS</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		2400		pF
$C_{oss}$	Output Capacitance			480		
$C_{rss}$	Reverse Transfer Capacitance			200		
<b>SWITCHING CHARACTERISTICS</b> (Note 1)						
$t_{D(on)}$	Turn - On Delay Time	$V_{DD} = 10\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\ \Omega$		13	24	nS
$t_r$	Turn - On Rise Time			14	26	
$t_{D(off)}$	Turn - Off Delay Time			43	70	
$t_f$	Turn - Off Fall Time			15	27	
$Q_g$	Total Gate Charge	$V_{DS} = 15\text{ V}, I_D = 30\text{ A}$ $V_{GS} = 5\text{ V}$		23	33	nC
$Q_{gs}$	Gate-Source Charge			7		
$Q_{gd}$	Gate-Drain Charge			11		
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>						
$I_S$	Maximum Continuous Drain-Source Diode Forward Current (Note 1)				60	A
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current (Note 1)				180	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 30\text{ A}$ (Note1)		1	1.3	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_F = 30\text{ A}$ $di_F/dt = 100\text{ A}/\mu\text{s}$		22	50	ns
$I_{rr}$	Reverse Recovery Current			0.79	5	

**Notes**

 1. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

## Typical Electrical Characteristics

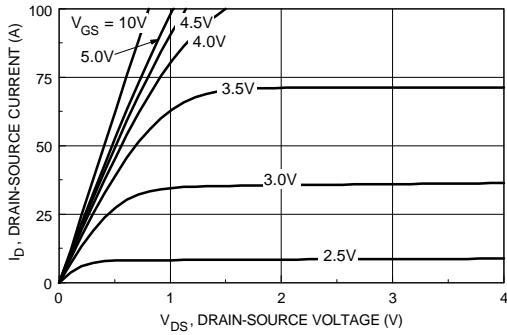


Figure 1. On-Region Characteristics.

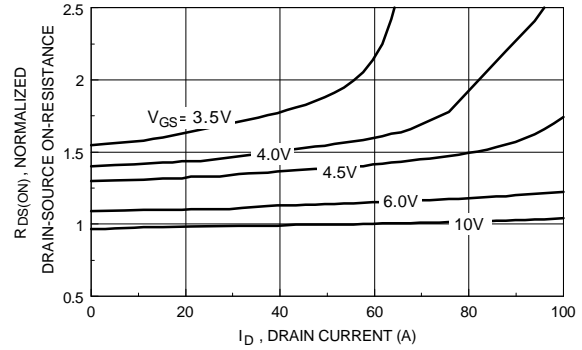


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

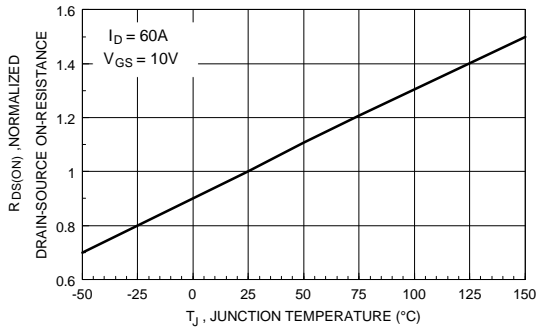


Figure 3. On-Resistance Variation with Temperature.

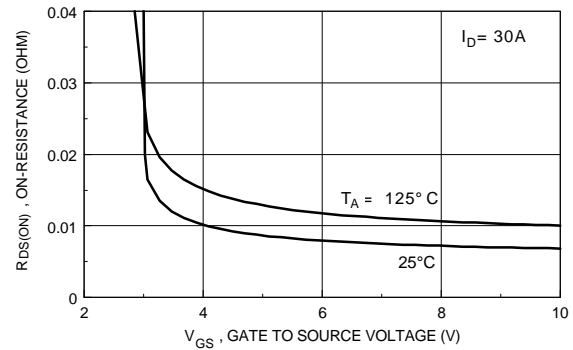


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

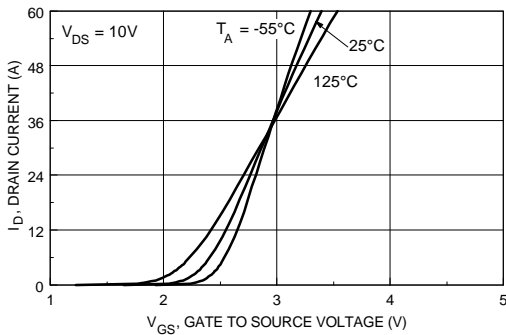


Figure 5. Transfer Characteristics.

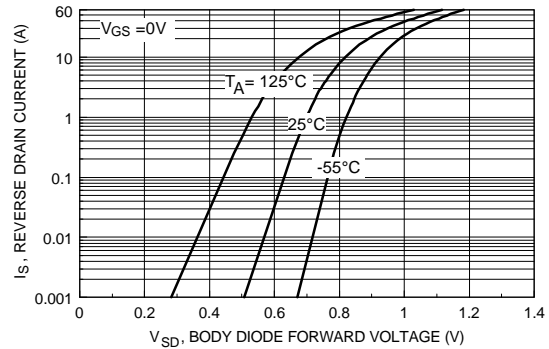


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

### Typical Electrical Characteristics (continued)

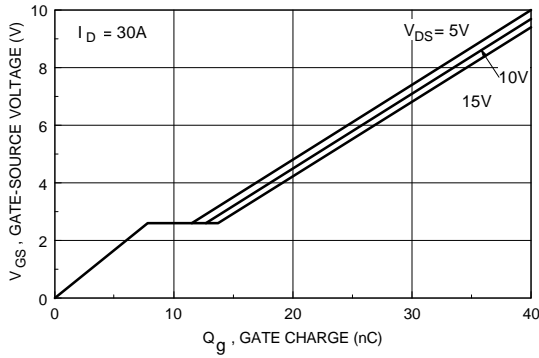


Figure 7. Gate Charge Characteristics.

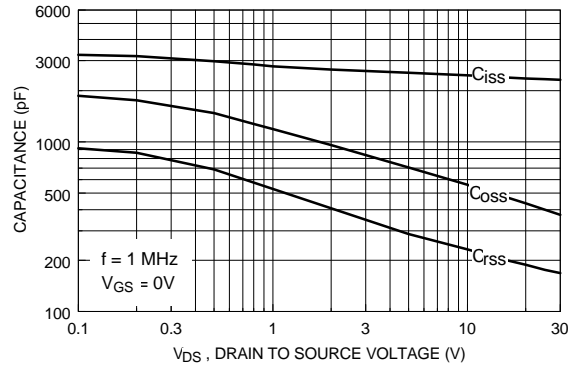


Figure 8. Capacitance Characteristics.

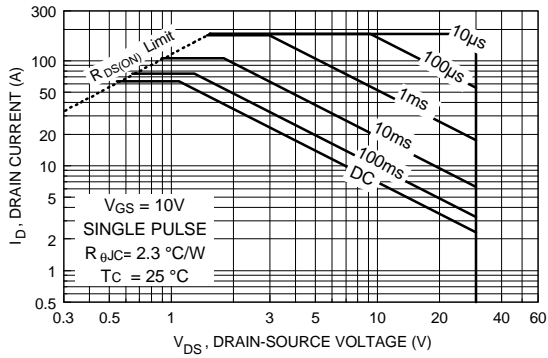


Figure 9. Maximum Safe Operating Area.

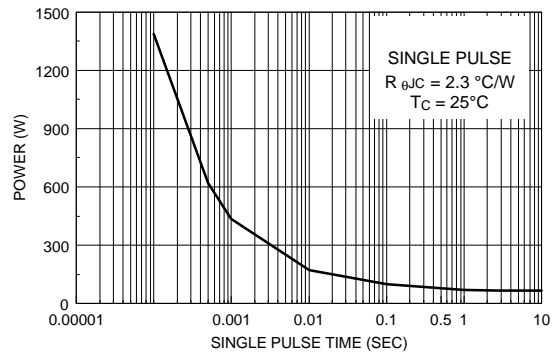


Figure 10. Single Pulse Maximum Power Dissipation.

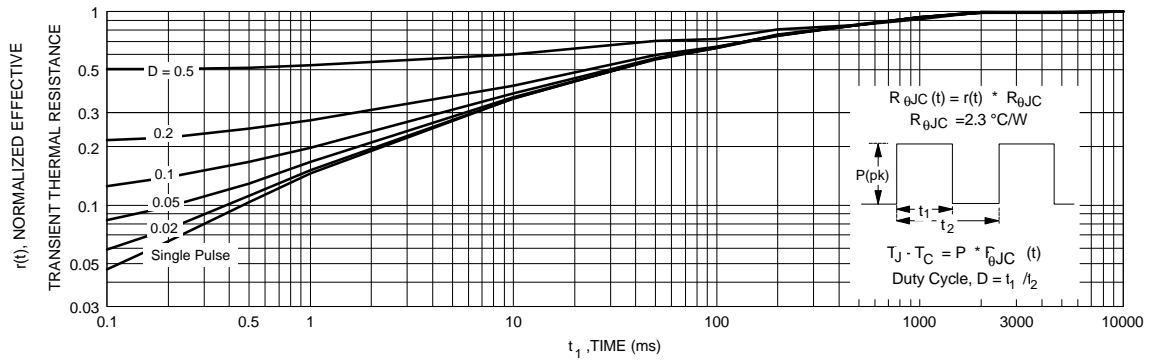


Figure 11. Transient Thermal Response Curve.

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